

Sheet 1 of 7

FORM PTO-1449  
(REV. 6-89)U.S. DEPARTMENT OF COMMERCE  
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Attorney's Docket No.

22920-06460

Serial No.

10/087,408

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Xiaodong Huang et al.

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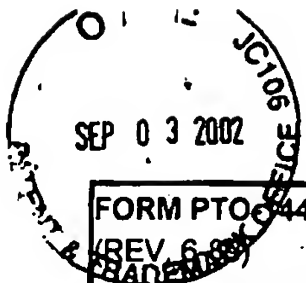
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<b>EXAMINER:</b> Initial if references considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	



Sheet 7 of 7

FORM PTO-1449 (REV. 6-89) <b>INFORMATION DISCLOSURE CITATION</b>  (Use several sheets if necessary)	U.S. DEPARTMENT OF COMMERCE Patent and Trademark Office	Attorney's Docket No. 22920-06460	Serial No. 10/087,408
	Applicant Xiaodong Huang et al.		
	Filing Date March 1, 2002	Group Art Unit Unassigned	

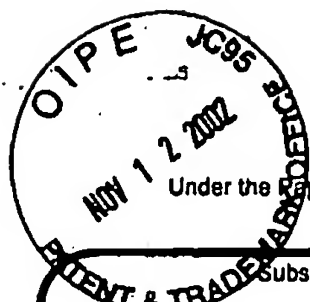
**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER <i>James Davis</i>	DATE CONSIDERED <i>2/02/04</i>
EXAMINER: Initial if references considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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REV: 02/01

22920/06460/DOCS/1256916.1



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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

**Complete if Known**

Application No.	10/087,408
Filing Date	March 1, 2002
First Named Inventor	Xiaodong Huang
Art Unit	2881
Examiner Name	Not yet known
Attorney Docket Number	22920-06460

Sheet 1 of 1

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JSD	C	US-5,557,627	09/17/1998	Schneider, Jr. et al.
JSD	D	US-5,710,436	01/20/1998	Tanamoto et al.
JSD	E	US-5,714,765	02/03/1998	Noetzel et al.
JSD	F	US-5,881,086	03/09/1999	Miyazawa
JSD	G	US-5,953,356	09/14/1999	Botez et al.
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JSD	J	US-6,285,704	09/04/2001	Kullander-Sjoberg et al.
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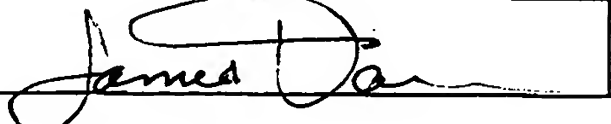
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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> - Number <sup>4</sup> Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	T <sup>6</sup>

**OTHER REFERENCES - NON-PATENT LITERATURE DOCUMENTS**

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JSD	L	U.S. Patent Application Publication, US 2001/0050934, December 13, 2001; Choquette et al.	

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Examiner Signature		Date Considered	2/03/04
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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Complete if Known

Application N .	10/087,408
Filing Date	March 1, 2002
First Named Inventor	Xiaodong Huang
Art Unit	2828
Examiner Name	James W. Davie
Attorney Docket Number	22920-06460

Sheet

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of

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### U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Document No. Number - Kind Code <sup>2</sup> (if known)	Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
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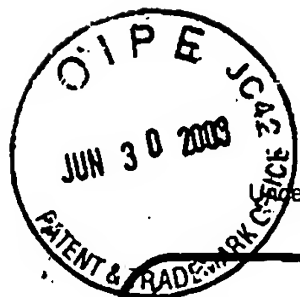
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>				Application No.	10/087,408
				Filing Date	March 1, 2002
				First Named Inventor	Xiaodong Huang
				Art Unit	2828
				Examiner Name	James W. Davie
Sheet	2	of	2	Attorney Docket Number	22920-06460

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>				Application No.	10/087,408
				Filing Date	March 1, 2002
				First Named Inventor	Xiaodong Huang
				Art Unit	2828
				Examiner Name	James W. Davie
Sheet	1	of	1	Attorney Docket Number	22920-06460

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